

FEATURES

- 10 mm X 10 mm active area
- Low dark current & capacitance
- Fast rise times
- High QE at 1064 nm

DESCRIPTION

100 mm² NIR enhanced PIN Photodiode. Package features a BNC connector and a borosilicate window.

APPLICATIONS

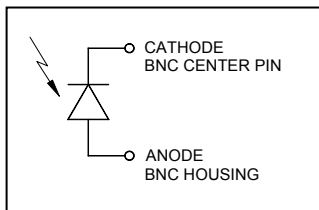
- Pulsed 1064 nm laser detection
- NIR pulsed light sensor
- High speed photometry



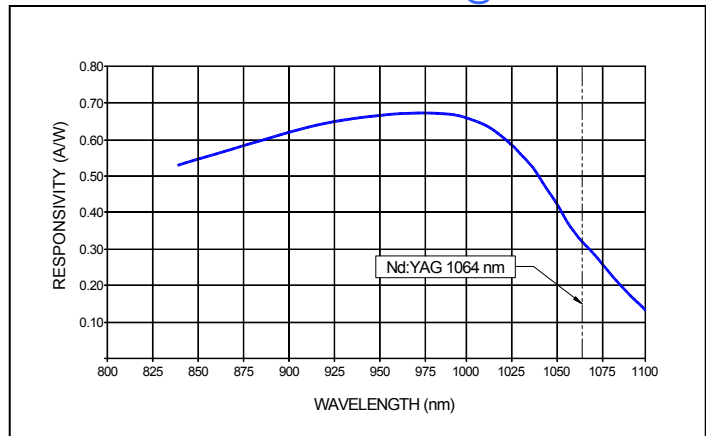
ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS
T _{STG}	Storage Temp	-20	+80	°C
T _{OP}	Operating Temp	-20	+60	°C
V _{R(OP)}	Reverse Operating Voltage	-	50	V
I _(PEAK)	Peak DC Current	-	10	mA

SCHEMATIC



SPECTRAL RESPONSE @ 23°C



ELECTRO-OPTICAL CHARACTERISTICS @ 23°C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _D	Dark Current	V _R = 150 V; @ 23°C	---	80	---	nA
		V _R = 150 V; @ 60°C	---	1.2	---	µA
C	Capacitance	V _R = 150 V	---	100	---	pF
	Responsivity	V _R = 150 V; λ = 1064 nm; @ 23°C	---	0.30	---	A/W
		V _R = 150 V; λ = 1064 nm; @ 60°C	---	0.40	---	
V _{BR}	Breakdown Voltage	I _R = 10 µA	200	---	---	V
t _r	Rise Time	V _R = 150 V; λ = 1064 nm; RL = 50 Ω	---	6	---	ns

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

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